

500mA 30V low VF(0.51mm)

Chip Information

Chip Size	0.51 x 0.51mm
Pad Size	0.41 x 0.41mm
Chip Quantity	42340 pcs/wafer
Scribe Line Width	40um
Passivation	PSG
Wafer Size	5inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	30	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	20	V	
Average Forward Rectified Current	IF(AV)	500	mA	
Peak Forward Surge Current	IFSM	5	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.470	0.440	0.410	V	IF=500mA Ta=25degC
	VF2	0.360	0.337	0.280	V	IF=100mA Ta=25degC
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	100	50	31	uA	VR=20V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	30	35	44	V	IR=500uA
Junction Capacitance	Cj				pF	
Reverse Recovery Time	trr				nS	

Ordering Information

Chip Type	Chip Thickness	Back Metal
YFG105	180 +/- 20um	Au(For Eutectic)
YFG107	150 +/- 20um	Au(For Eutectic)
YFG106	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:
Designed For RB551V-30